NSN 5962-01-310-1464

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View Online at https://aerobasegroup.com/nsn/5962-01-310-1464

Body Length:
0.840 inches
Body Width:
Between 0.220 inches and 0.310 inches
Body Height:
Between 0.140 inches and 0.185 inches
Maximum Power Dissipation Rating:
794.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and burn in and schottky and monolithic
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
10 input
Case Outline Source And Designator:
D-2 mil-m-38510
Current Rating Per Characteristic:
140.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
85.00 nanoseconds delay
85.00 nanoseconds delay Memory Device Type:
Memory Device Type:
Memory Device Type: Prom
Memory Device Type: Prom Test Data Document:
Memory Device Type: Prom Test Data Document: 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Memory Device Type: Prom Test Data Document: 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). Terminal Type And Quantity:
Memory Device Type: Prom Test Data Document: 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). Terminal Type And Quantity: 16 printed circuit

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Demilitarization:

Yes - demil/mli

Fiig:

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